AN1101SSM

CMOS single power supply

Overview

AN1101SSM is an operational amplifier with a single power supply by CMOS diffusion process.

It has low current-consumption compared to general purpose operational amplifier by bipolar diffusion process. 0 V to V_{DD} is available for both input voltage and output voltage. And this IC is widely applicable to the buttery-driven equipment and to many amplifier circuits which adopt small package products.

Features

• Low current-consumption: $I_{DD} = 55 \mu A$ (typ.), $V_{DD} = 3 V$

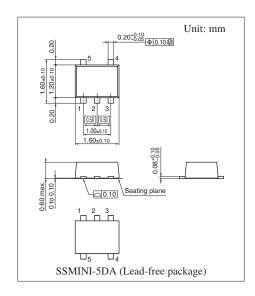
 \bullet Operating input/output voltage range: 0 V to V_{DD}

• Small offset voltage: 0.5 mV (typ.)

• Small input bias current: 1 pA (typ.)

• Operating supply voltage range:

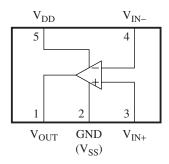
2.5 V to 5.5 V or ± 1.25 V to ± 2.75 V



Applications

• Various small-size general consumer electronics equipment

Block Diagram



Pin Descriptions

Pin No.	Symbol	Description			
1	V _{OUT}	Output			
2	GND (V _{SS})	Ground, V_{SS} (negative supply) at using two power supply			
3	V _{IN+}	Input (positive)			
4	V_{IN-}	Input (negative)			
5	V_{DD}	Power supply			

Note) The AN1101SSM has been designed for general consumer electronics equipment, not for the specific one requiring such a high reliability that may prevent it from threatening the human lives.

■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V_{DD}	5.6	V
Differential input voltage	DV _{IN}	±5.6	V
Input voltage	V _{IN}	V _{SS} to V _{DD}	V
Supply current	I_{DD}	_	mA
Power dissipation *2	P_{D}	50	mW
Operating ambient temperature *1	T _{opr}	-30 to +85	°C
Storage temperature *1	T_{stg}	-55 to +125	°C

Note) 1. \pm 1: Except for the operating ambient temperature and storage temperature, all ratings are for $T_a = 25^{\circ}\text{C}$.

■ Recommended Operating Range

Parameter	Symbol	Range	Unit
Supply voltage	V_{DD}	2.5 to 5.5	V
		±1.25 to ±2.75	

■ Electrical Characteristics at $V_{DD} = 3.0 \text{ V}$, $V_{SS} = GND$, $T_a = 25^{\circ}C \pm 2^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input offset voltage	V _{IO}	Buffer circuit	_	0.5	5.5	mV
Common-mode input voltage	CMV _{IN}	$R_S = 10 \text{ k}\Omega, R_F = 10 \text{ k}\Omega$	0	_	3	V
Open-loop gain	GV	f = 100 Hz	60	90	_	dB
Maximum output amplitude voltage 1	V _{OH}	$R_L \ge 10 \text{ k}\Omega$	2.90	2.98	_	V
Maximum output amplitude voltage 2	V _{OL}	$R_L \ge 10 \text{ k}\Omega$	_	0.01	0.05	V
Common-mode input voltage rejection ratio	CMRR	$V_{IN} = 0.0 \text{ V to } 3.0 \text{ V}, R_S = R_F = 10 \text{ k}\Omega$	50	65	_	dB
Supply voltage ripple rejection ratio *	SVRR	$V_{DD} = 2.5 \text{ V to } 5.5 \text{ V}$	55	70		dB
Supply current	I_{DD}	No load		55	100	μΑ

Note) * : Except for the supply voltage ripple rejection ratio (SVRR), $V_{DD} = 3 \text{ V}$.

• Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Reference	Unit
Offset current	I _O	_	1	pA
Input bias current	I _{IO}	_	1	pA
Slew rate	SR	$R_L \ge 10 \text{ k}\Omega$	0.35	V/µs
Zero-cross frequency	f_T	$A_V = 1$	0.8	MHz

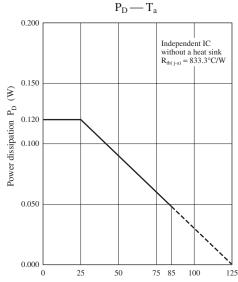
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^{*2:} The value at $T_a = +85$ °C.

^{2.} This IC is not suitable for car electrical equipment.

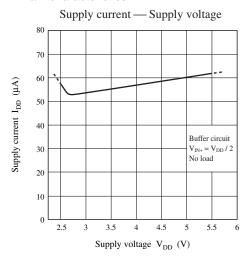
■ Technical Data

• P_D — T_a curve of SSMINI-5DA

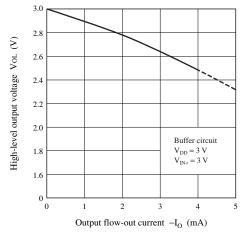


Main characteristics

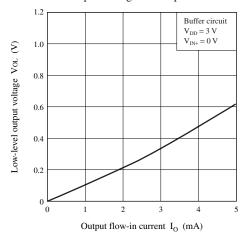
Ambient temperature T_a (°C)



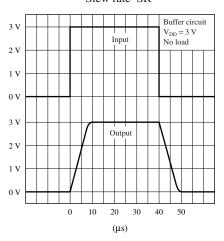
High-level output voltage — Output flow-out current



Low-level output voltage — Output flow-in current



Slew rate SR

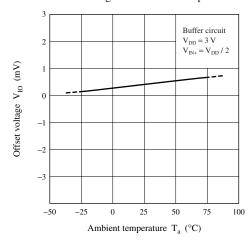


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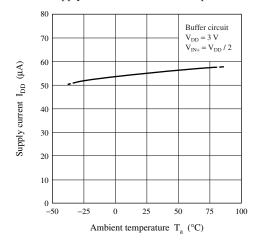
■ Technical Data (continued)

• Main characteristics (continued)

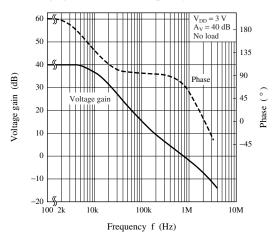
Offset voltage — Ambient temperature



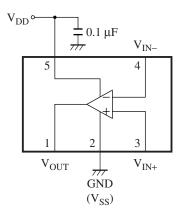
Supply current — Ambient temperature



Voltage gain · Phase — Frequency characteristics



■ Application Circuit Example



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